Isolation Voltage	V_{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T_{jmax}				175	
Operating Junction Temperature	$T_{vj\ op}$		-40		150	
Storage Temperature	T_{stg}		-40		150	
Comparative Tracking Index	CTI		400			
Thermal Resistance Junction to Case	$R_{\theta JC}$	per IGBT			0.12	K/W
		per Diode			0.21	
Thermal Resistance Case to Sink	$R_{\theta CS}$	Conductive grease applied		0.012	0.035	K/W

Module Electrodes Torque

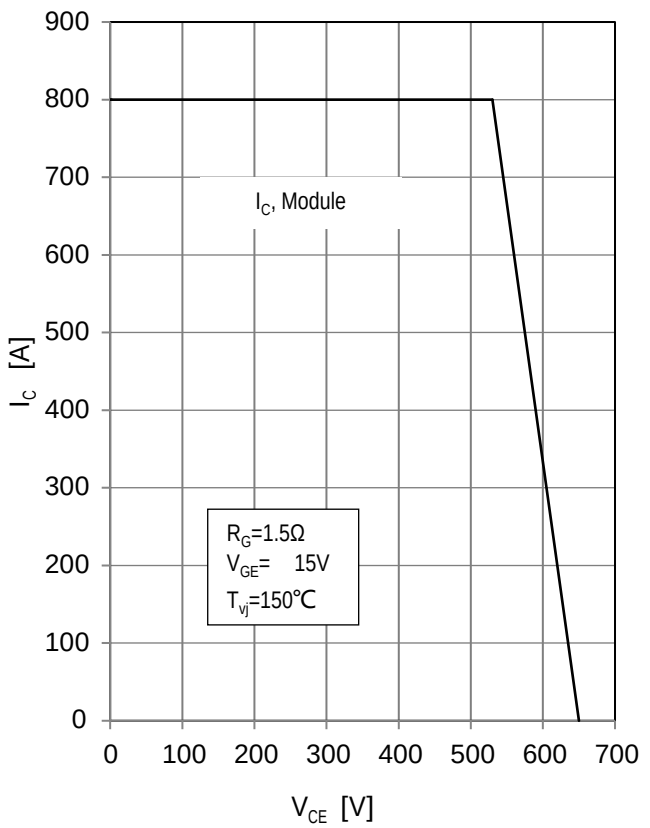

Fig5. RBSOA

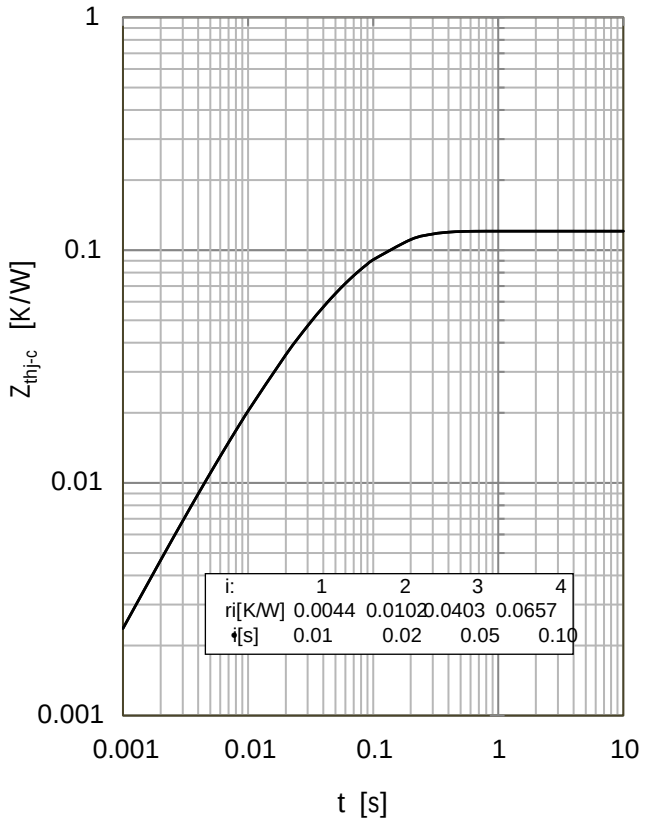

Fig 6. IGBT Transient Thermal Impedance

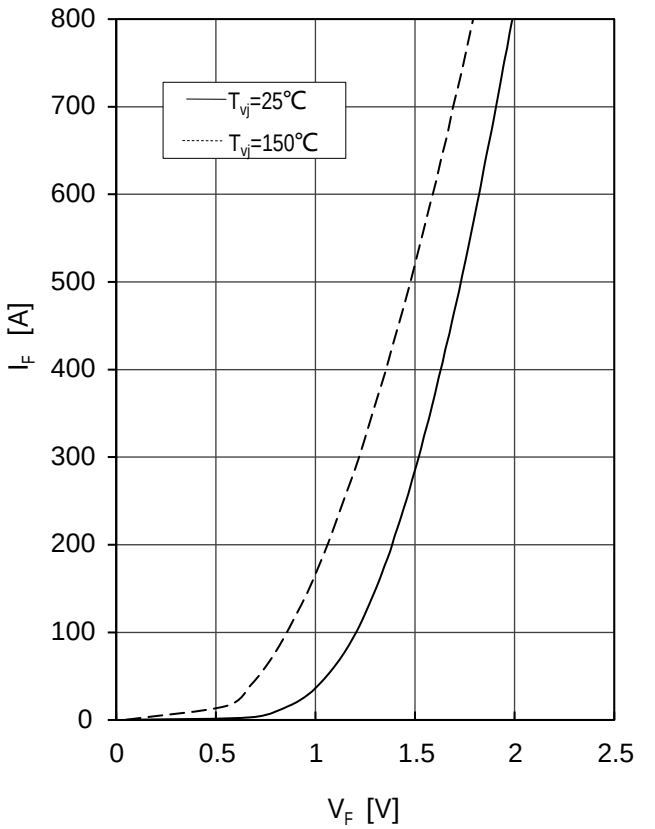

Fig7.Diode Foward Characteristics

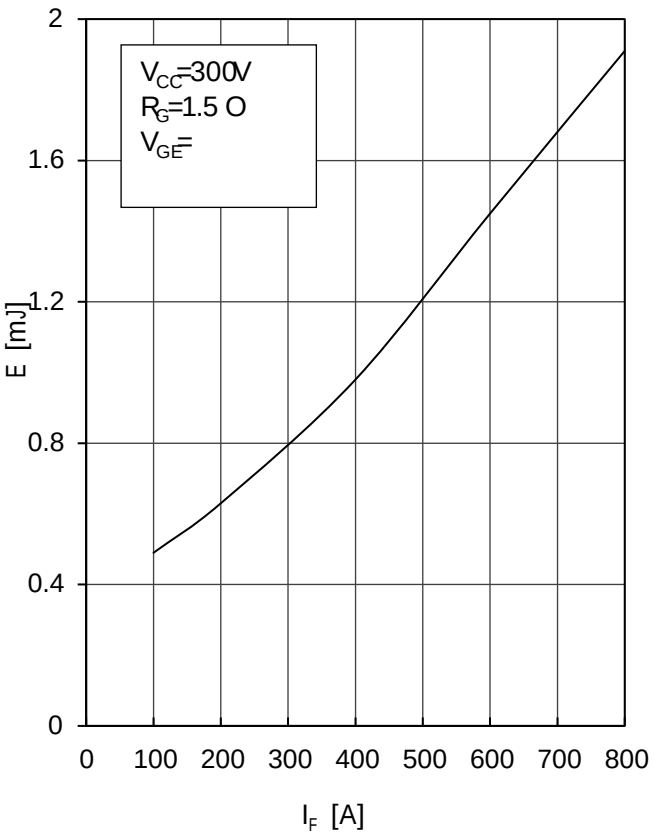

Fig8.Diode Switching Loss vs.I_F

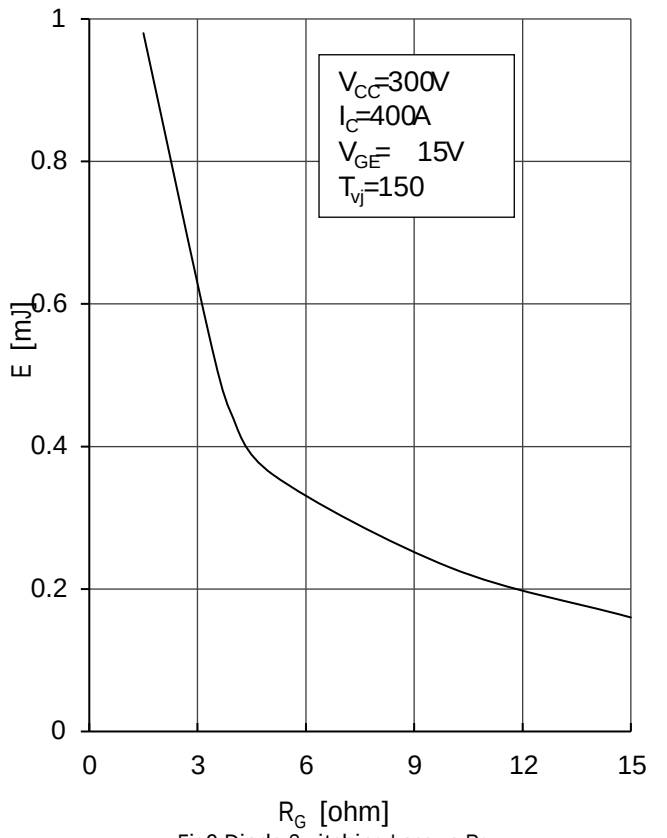

Fig9.Diode Switching Loss vs.Rg

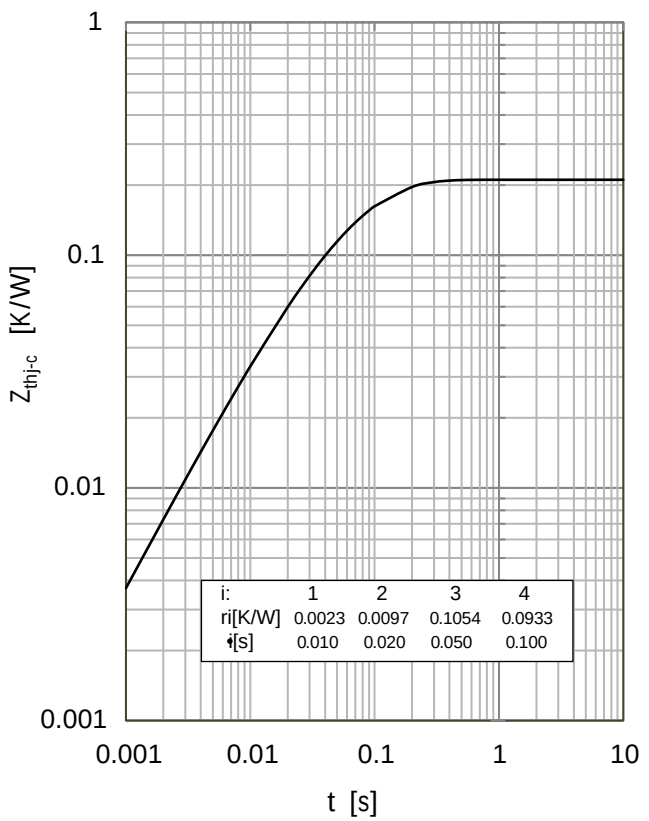

Fig10.Diode Transient Thermal Impedance